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Kind regards,

Team Nexperia



 150 V, 1 A PNP high-voltage low VCEsat BISS transistor

 16 January 2017

**Product data sheet** 

#### 1. General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8115TLH

#### 2. Features and benefits

- High voltage •
- Low collector-emitter saturation voltage V<sub>CEsat</sub> •
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Small SMD plastic package
- AEC-Q101 qualified •

#### 3. Applications

- Power management •
- LCD backlighting
- LED driver for LED chain module •
- Switch Mode Power Supply (SMPS) •

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-150	V
I <sub>C</sub>	collector current			-	-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-	-2	А
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C		70	-	300	



150 V, 1 A PNP high-voltage low VCEsat BISS transistor

### 5. Pinning information

Table 2. F	Fable 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	В	base	3	C .				
2	E	emitter		вщ				
3	С	collector	1 2 TO-236AB (SOT23)	E sym132				

### 6. Ordering information

Table 3. Ordering information						
Type number	Package	ackage				
	Name	Description	Version			
PBHV9115TLH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

### 7. Marking

Table 4. Marking codes					
Type number	Marking code <sup>[1]</sup>				
PBHV9115TLH	FC%				

[1] % = placeholder for manufacturing site code

150 V, 1 A PNP high-voltage low VCEsat BISS transistor

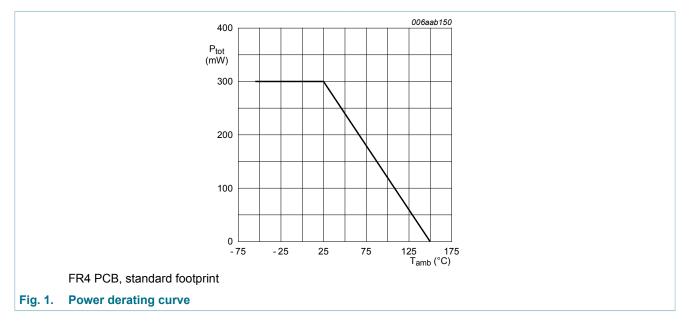
### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-150	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-200	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	А
I <sub>BM</sub>	peak base current			-	-400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

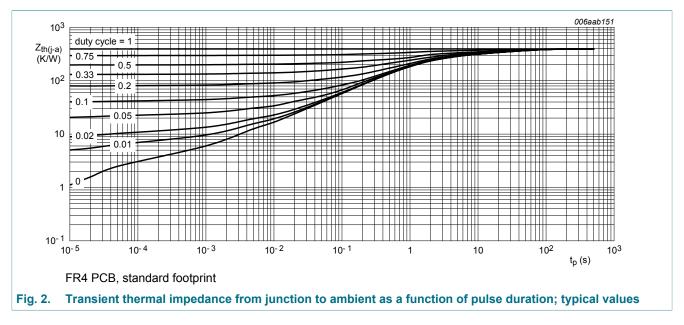


150 V, 1 A PNP high-voltage low VCEsat BISS transistor

#### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



150 V, 1 A PNP high-voltage low VCEsat BISS transistor

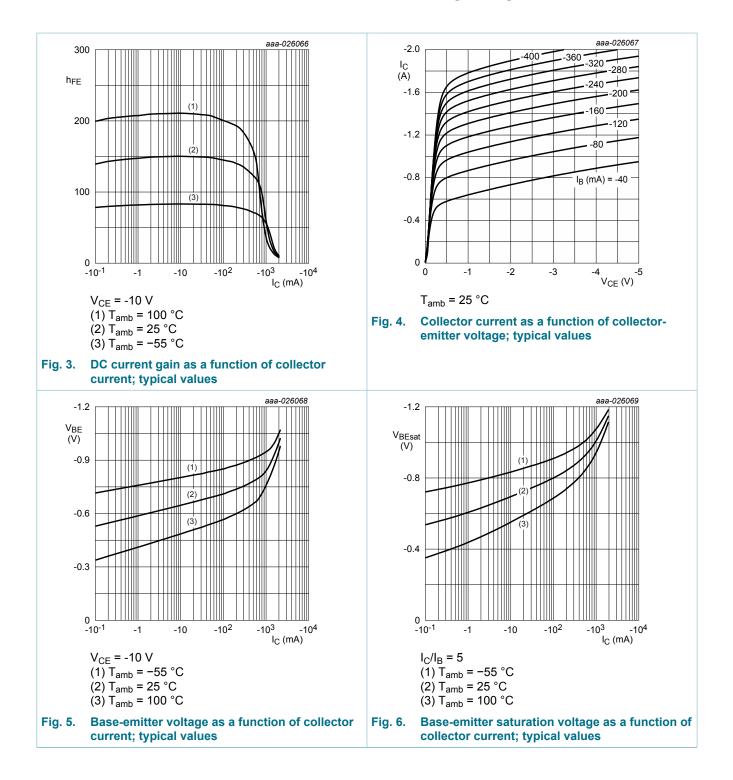
#### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -120 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C	70	-	300	
		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	60	-	300	
		$\label{eq:V_CE} \begin{array}{l} \text{V}_{\text{CE}} = \text{-10 V; } \text{I}_{\text{C}} = \text{-500 mA; pulsed; } \text{t}_{\text{p}} \leq \\ \text{300 } \mu\text{s; } \delta \leq \ \text{0.02 } \ \text{; } \text{T}_{\text{amb}} = \text{25 }^{\circ}\text{C} \end{array}$	50	-	300	
		$    V_{CE} = -10 \text{ V; } I_C = -1 \text{ A; pulsed; } t_p \leq \\     300 \ \mu\text{s; } \delta \leq 0.02 \ \text{; } T_{amb} = 25 \ ^\circ\text{C} $	10	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -100 mA; $I_{B}$ = -10 mA; $T_{amb}$ = 25 °C	-	-	-120	mV
		$I_{C}$ = -100 mA; $I_{B}$ = -20 mA; $T_{amb}$ = 25 °C	-	-	-100	mV
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-	-300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$\label{eq:IC} \begin{array}{l} \textbf{I}_{C} = -1 \text{ A}; \text{ I}_{B} = -200 \text{ mA}; \text{ pulsed};  \textbf{t}_{p} \leq \\ 300  \mu\text{s}; \delta \leq 0.02 \hspace{2mm} ;  \textbf{T}_{amb} = 25 ^{\circ}\text{C} \end{array}$	-	-	-1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -6 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -0.1 mA;	-	10	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.1 mA; T <sub>amb</sub> = 25 °C	-	285	-	ns
t <sub>on</sub>	turn-on time		-	295	-	ns
t <sub>s</sub>	storage time		-	430	-	ns
t <sub>f</sub>	fall time		-	300	-	ns
t <sub>off</sub>	turn-off time		-	730	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; I <sub>C</sub> = -10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	55	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	10	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	150	-	pF

#### **NXP Semiconductors**

### PBHV9115TLH

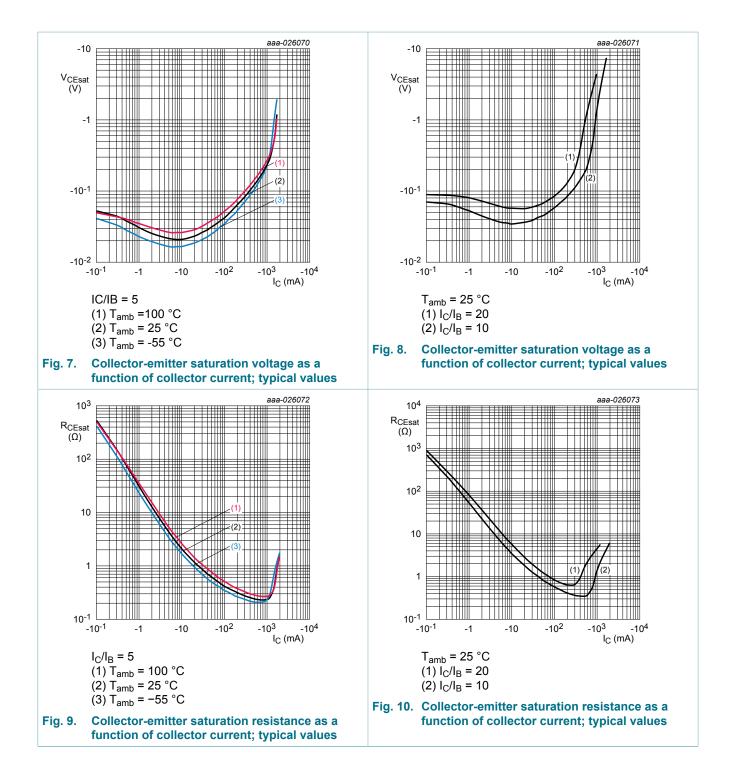
#### 150 V, 1 A PNP high-voltage low VCEsat BISS transistor



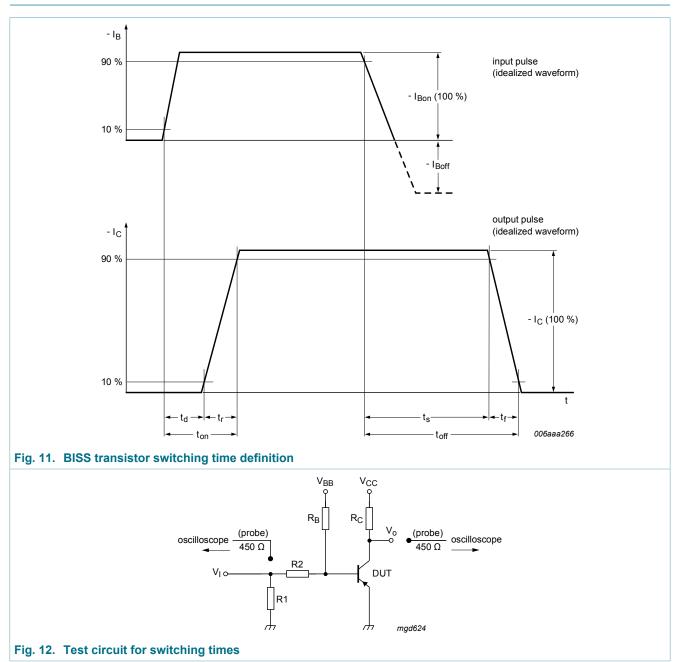
#### **NXP Semiconductors**

### PBHV9115TLH

#### 150 V, 1 A PNP high-voltage low VCEsat BISS transistor



#### 150 V, 1 A PNP high-voltage low VCEsat BISS transistor



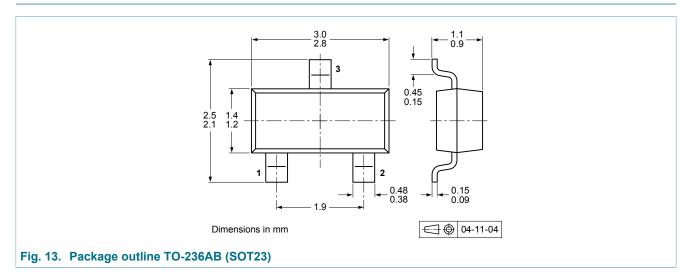
#### 11. Test information

#### **Quality information**

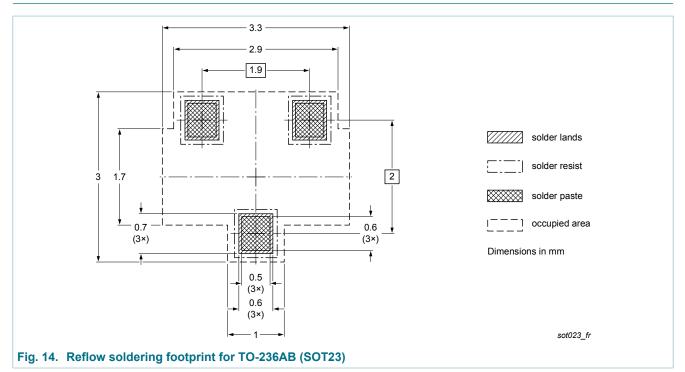
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 150 V, 1 A PNP high-voltage low VCEsat BISS transistor

#### 12. Package outline

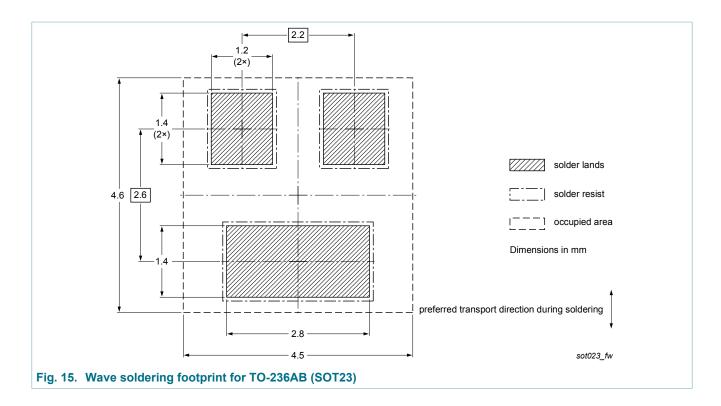


#### 13. Soldering



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#### 150 V, 1 A PNP high-voltage low VCEsat BISS transistor



PBHV9115TLH

150 V, 1 A PNP high-voltage low VCEsat BISS transistor

### 14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBHV9115TLH v.1	20170116	Product data sheet	-	-	

#### 150 V, 1 A PNP high-voltage low VCEsat BISS transistor

#### 15. Legal information

#### **Data sheet status**

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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